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Contents

Plenary

K.1	The Complete Semiconductor Transistor Profs. Sah Chihtang and Jie Binbin, China and USA	P1
K.2	The future development of mixed signal IC in nanotechnology Dr. Byeong-Ha (Paul) Park, Samsung Electronics, Kr	P2
Ad	vanced CMOS Structure	
1.1	Modeling and Characterization of Radio-Frequency Characteris of Multi-Finger Nanometer MOS Transistors Hei Wong, City University, Hong Kong, China	stics P3
1.2	A More Accurate Potential-Based Drain Current Model Bulk-MOSFETs Yucong Huang, Xinnan Lin, Jian Zhang, Hao Zhuang	for P8
1.3	Process Integrated of High Aspect Ratio Copper Dual Damase Process Chun-Jen Weng	cene P12
1.4	An Analytical Current Model for Lateral Gradual Doping Chann LDMOS Wenniu Xie, Bin Li	el in P16
1.5	An Improved Copper Interconnect TDDB Lifetime Model Du Ming, Ma Peijun, Li Siyan, Hao Yue	P20
RF	Circuits	
2.1	A Low-Voltage Low-Power Self-mixer for 3.1-5GHz Non-cohe	rent

- **UWB Receiver** P24

 Wei Wu, Cameron T. Charles, Tingcun Wei , Xiaoya Fan
- 2.2 Analysis and Design of Class E Power Amplifier employing SiC MESFETs P28 Zhichao Xu, Hongliang Lü, Yuming Zhang, and Yimen Zhang
- 2.3 Design of CRLH Millimeter-Wave Passive Filters in Standard CMOS Process P32

Y. Zhang, N. H. W. Fong and N. Wong

2.4 Switched-Capacitor Based RF Mixer Alejandro de la Plaza

2.5 RF front-end ICs for Digital Radio Broadcasting DRM and DAB P39 K. P. Wang, Z. G. Wang, X. M. Lei, J. Z. Zhou, X. Cao and W. R. Zhang

Nanowire and Multigate MOSFETs

- 3.1 ULTRA-SOI: New generation of SOI-MOSFET model with physics based dynamic depletion characteristics P44 Jin He, Peking University, China
- 3.2 Optimization of Sub-100nm Transistor Gate Sidewall Spacer Process for High-Performance Applications P50 Chun-Jen Weng
- 3.3 Numerical Simulation Study on Electron Mobility of Independent DG MOSFETs P54

Lin Chen, Yiwen Xu, Lining Zhang, Wang Zhou, Frank He

- 3.4 Generic DG MOSFET Analytic Model with Vertical Electric Field Induced Mobility Degradation Effects P58 Xingye Zhou, Lining Zhang, Jian Zhang, Frank He, and Xing Zhang
- **3.5** Performance Analysis of Dual-Material Gate SOI MOSFETP63Hongxia Liu, Qianwei Kuang, Suzhen Luan, Yue Hao
- 3.6 The Effects of Random Distribution Fluctuations of Dopants on SOI-MOSFET Performance P67 Jafar Ahadzadeh Farhood Bonab; Seyed Ehsan Abtahi; Seyed Ebrahim Hosseini
- **3.7** Modeling SOI-MOSFET Using Neuro Space MappingP71Mahdi Gordi Armaki, Seyed Ebrahim Hosseini and Javad Haddadnia
- 3.8 A Physical Model Based on Surface Potential for Double-Gate a-Si:H TFTs P75

Yuan Liu, Ruo-He Yao, Bin Li and Wen-Niu Xie

Data Conversion Circuits

- 4.1 An 8-b 600MSmaples/s Folding and Interpolating ADCP79Yunhua Yu, Weining Ni, Xubing Zhu, Haitao Shi, Na Qi
- 4.2 Design technique for SMDAC without aperture error for 14-b100MS/s pipelined ADC applicationsP83Zhaoxin Xiong, min CAI

- 4.3 A Single-Inductor Dual-Output Buck Converter with Self-Adapted PCCM Method P87 Yang Yang, Sun Liang, Wu Xiaobo
- **4.4 Digital Static Calibration Technology Used for 400MSPS, 16-bit DAC** Zhu Dongmei, Fu Dongbing, Shi Jiangang and Li Kaicheng **P91**
- 4.5 A Novel Method for Smooth Transition in Step-Up/Step-Down DC-DC Converter P95

Yanzhao Ma, Hongyi Wang, Guican Chen and Fan Qu

High Voltage Circuit and ESD

5.1	A Novel E-SIMOX High Voltage Device Structure with the Islands on the SOI Lijuan WU, Shengdong Hu, Bo Zhang and Zhaoji Li	Charge P99
5.2	A Novel SOI IGBT for Power-Rail ESD Clamp Circuit Jing Zhu , Qinsong Qian, Weifeng Sun	P103
5.3	Power Rail ESD Circuit Simulation and Verification Li Zhiguo, Yue Suge and Sun Yongshu	P107
5.4	A Novel ESD Power Clamp Circuit with TSPCL D Flip-flop Baojun Tang, Hongxia Liu	P111
5.5	Ultra Low-Power Full-Adder for Biomedical Applications Eng Sue Chew, Myint Wai Phyu, and Wang Ling Goh	P115

NEMS, MEMS and Sensors

 6.1 MEMS Optically Differential Reconfigurable Gate Array Hironobu Morita and Minoru Watanabe
 6.2 Surface Recombination/ Generation Velocity in Metal-Oxide- Silicon Field-Effect Transistors Zuhui Chen, Xing Zhou, Guojun Zhu, and Shihuan Lin
 6.3 A Study on InGaN/GaN Multiple Quantum-Well Hydrogen Sensor with HfTiO as Gate Dielectric Gang Chen, A.H.W. Choi, P.T. Lai

Carbon Nanotube and Nanofiber Devices

- 7.1Contact resistances of carbon nanotube via interconnectsP131Xuhui Sun, Santa Clara University, USA
- 7.2 Transport properties of an (8, 0) carbon/silicon carbide nanotube heterojunction
 P136
 HongXia Liu, HeMing Zhang, Jiuxu Song
- 7.3 Nano magnetic column arrays fabrication forpatterned media in magnetic recordingusing EB lithography and ion milling P140 Sumio Hosaka, Yasunari Tanaka, Masumi Shirai, Zulfakri Mohamad, You Yin, Yuji Kondo, and Jun Ariake

Compound Semiconductor & Packaging

- 8.1 A Two-dimensional Analytical Subthreshold Behavior Model for Short-Channel Dual-Material Gate(DMG) AlGaAs/GaAs HFETs
 T. K. Chiang, National University of Kaohsuing, Taiwan, China P144
- 8.2 RF–DC Power Conversion of Schottky Diode Fabricated on AlGaAs/GaAs Heterostructure for On-Chip Rectenna Device Application in Nanosystem P150 Farahiyah Mustafa, Norfarariyanti Parimon, Shaharin Fadzli Abd Rahman, Abdul Manaf Hashim and Mohd Nizam Osman
- 8.3 Self-Formed Submicron-Scale Faceted Copper Particles on the Surface of Annealed Cu-Zr Films P154 Jingmei Zhan, Haoliang Sun, Fei Ma and Kewei Xu
- 8.4 Field Emission of ZnO Cathode Fabricated by Electrophoresis
 Yanning Yang, Zhiyong Zhang, Fuchun Zhang ,Weihu Zhang, Junfeng
 Yan

Digital Circuit

- 9.1 Digital Circuit Design for a High-Speed Direct Digital Frequency Synthesizer P162 Jinshan Yu, Ruitao Zhang,YuJing Li , Dongbing Fu, RuZhang Li, Yafeng Yao, Tun Li
- 9.2 A CMOS Bootstrapped Switch with Novel Clock Feed-through Compensation P166

Xiaofeng Wu , Hongxia Liu, Yi Wu

- 9.3 A16-bit312.5-kHzBandwidthFourth-orderOne-BitSwitched-Capacitor Sigma-Delta ModulatorP170Hongyi Li, Yuan Wang, Song Jia, and Xing Zhang
- 9.4 Dual Cycle Shift Data-Weighted Averaging Technique for Multi-Bit
Sigma-Delta ModulatorsP174
P174Xiaofen Ma, Jian Xu and Xiaobo WuP174
- 9.5 An Optimized Architecture of Cascaded Crossbar Switches in SoC Systems P178

Niu Jiuchong, Wang Xin'an, Lu Qingwang and Hu Ziyi

9.6 A Doppler Bins Elimination Algorithm in a GPS Signal Acquisition System P182

Weijun Lu, Ying Li, Dunshan Yu, Xing Zhang

9.7 Bit Synchronization Methods and Their Performance for HSGPS Receivers P186

Weijun Lu, Yongcan Huang, Lingjuan Wu, Dunshan Yu, Xing Zhang

- **9.8 An Efficient Clock Tree Synthesis Method in Physical Design P190** Guirong Wu, Song Jia, Yuan Wang, Ganggang Zhang
- 9.9 Defects Detecting of Copper Interconnects Based on Signal Reflection Theory
 P194

 Wen Zhou, Hongxia Liu, Jianjun Wei, Qianwei Kuang
 P194

High K Dielectric

- 10.1 Impact of Oxide Trap Charge on Performance of Strained Fully

 Depleted SOI Metal-Gate MOSFET
 P197

 W. K. Yeh, National University of Kaoshuing, Taiwan, China
- 10.2 Low-Voltage Polymer Thin-Film Transistors with High-k HfTiO GateDielectric Annealed in NH3 or N2P201L. F. Deng, H.W.Choi,P. T. Lai, Y.R.Liu and J. P. Xu
- 10.3 ZnO Based Thin-Film Transistor with High-к Gadolinium and Praseodymium Oxide as Gate Dielectric P205 Hsiang-Chun Wang, Che-Kai Lin, Hsien-Chin Chiu, and Kuang-Po Hsueh
- 10.4 Effects of Sputtering and Annealing Temperatures on
Capacitor with HfTiON Gate DielectricMOS
P209C.D. Wang, C.X. Li, C.H. Leung and P.T. Lai
- 10.5 Study on Electrical Characteristics of Amorphous InGaZnO MOS
Capacitors with High κ HfOxNy Gate DielectricP213
P213
P213Xingsheng Tong, Xiao ZouP213

- 10.6 Electrical properties of polycrystalline p-CuxO MOS capacitors with
SiO2/HfO2 high κ stack gate dielectric on Silicon substrateP217
P217Xiao Zou , Guojia Fang, Longyan Yuan, Nishuang Liu, and Hao Long
- 10.7 Impacts of Ti Content and Annealing Temperature on Electrical Properties of Si MOS Capacitors with HfTiON Gate Dielectric P221 F. Ji, J. P. Xu, C. X. Li, P. T. Lai, C. L. Chan
- 10.8 Optimization of N Content for Higk-k LaTiON Gate Dielectric of Ge MOS Capacitor P225 H. X. Xu, J. P. Xu, C. X. Li, P. T. Lai, C. L. Chan
- 10.9 Transport Mechanism of the Leakage Current in MIS Capacitor with HfO2/SiO2 Stack Gate P229 Qianwei Kuang, Hongxia Liu, Wen Zhou, Bo Gao, Aaron Zhao, Sai Tallavarjula
- 10.10 HfO2 Inter-Poly Dielectric Characteristics with Interface Fluorine
PassivationP233
P233
P233
Pung-Yu Chen, Chih-Ren Hsieh, Kwung-Wen Lu and Jen-Chung Lou
- 10.11 A Compact Threshold-Voltage Model of MOSFETs with Stack
High-k Gate DielectricP236F. Ji, J. P. Xu, J. J. Chen, H. X. Xu, C. X. Li, P. T. Lai
- 10.12 Reliability Improvement of HfO2/SiON Gate Stacked MOSFET
using Fluorinated Silicate Glass Passivation LayerP240Chih-Ren Hsieh, Yung-Yu Chen, Jer-Fu Chung and Jen-Chung Lou
- 10.13 Effects of annealing gas species on the electrical properties and reliability of Ge MOS capacitors with high-k Y2O3 gate dielectric C.X. Li, H.X. Xu, J.P. Xu, P.T. Lai P243

Analog Circuits

11.1 Compct UWB Bandpass Filter Using Microstrip and Co Waveguide Back-to-back Coupled Structure Jianguo Ma, University of Electronic Science and Technology, China	planar P247
11.2 A Novel Gate Boosting Circuit for 2-Phase High Voltage Charge Pump Oi-Ying Wong, Wing-Shan Tam, Chi-Wah Kok and Hei Wong	CMOS P250
11.3 New Noise-Tolerant Dynamic Circuit Design Wei Su, Song Jia, Xiayu Li, Limin Liu, Yuan Wang	P254
11.4 A Pseudo-pipelined VLSI Architecture of Two Elliptic Curve Multiplications Wang Xu and Zhang Yan	Scalar P258

(litter Model of Fraction-N S Quantization Noise Huibin Tao, Yixin Guo And Zhibiao S	•	Influenced	by ΣΔ Ρ262
11.6 Analysis on the effect of regression and correlation models on the accuracy of Kriging model for ICP266Wang Hailang, You Hailong, Jia Xinzhang				
11.7	A New Model of Phase Noise Oscillators Jinhua Liu, Guican Chen, and Jian	•	LC-Tank Qu	adrature P270
11.8	An RC Oscillator with Tempera Delay Control in Electronic Deto Qinyu Zhou, Liming Li, and Guican	onators	nsation for <i>i</i>	Accurate P274
11.9	A High Gain Lateral BJT on Thin Faranak Homayoni, Seyed Ebrahir			P278
11.10	1.8 V CMOS Low Noise CPPLL D Huibin Tao, Pengzhan Zhang, Zhib	•		P282

SiC Materials & Devices

12.1	Recent progress in research of structural defects in 6H-SiC	single
	crystals	P287
	Xiangang Xu from Shandong University, Shandong, China	

- 12.2 The Effect of Surface Charge on the breakdown Behaviors of SiC

 SBD with planar terminations
 P291

 Song Qing-wen, Zhang Yu-ming, and Zhang Yi-men, Wang Zhang-xu
- 12.3 Thickness determination of 4H-SiC Epitaxial Films by Infrared Reflectance P295

Xiaoyan Tang, Yuming Zhang, Zhiyun Li and Yimen Zhang

- 12.4 Mechanism of conversion and propagation of dislocations in 4H-SiC epilayer P298 Ruixia Miao, Yuming Zhang, Yimen Zhang, Xiaoyan Tang and Qingfeng Gai
- 12.5 Optoelectronic Characteristics Simulation and Analysis of p-n
Si/6H-SiC HeterojunctionP302
P302Shunfeng Zhao, Zhiming Chen, Lianbi Li, Yuan Zang

Shuhleng Zhao, Zhinning Chen, Liandi Li, Tuan Zang

12.6 The preparation and Optoelectronic Characteristics of the p-n Si/SiC heterojunction P306

Yuan Zang, Zhiming Chen, Lianbi Li, Shunfeng Zhao

 12.7 Structure Design and Characteristics Analysis of 4H-SiC PiN Switching Diodes P310 Jiayang Zhang, Yuming Zhang, Yimen Zhang, and Xiaoyan Tang
 12.8 Annealing effects on structural, optical and electrical properties of Al implanted 4H-SiC P314

Mingkun Zhang, Jun Huang, Rongdun Hong, Xiaping Chen, Zhengyun Wu

- 12.9 The Simulation Study of Gaussian-doped Base 4H-SiC Bipolar
Junction TransistorP318Jiaxuan Li, Yuming Zhang, Yimen Zhang and Xiaoyan Tang
- 12.10 Evolution of the Native Defects in Unintentionally Doped 4H-SiC during Annealing Process
 P322

 Ping Cheng Yuming Zhang, Yimen Zhang, Hui Guo
 P322
- 12.11 A Simulation of DC and AC performance of 4H-SiC Tunneling
Emitter Bipolar Transistor (TEBT)P326Jing Liu, Yuming Zhang , and Yimen ZhangP326
- 12.12 The Simulation Study of 6H-SiC Photoconductive Semiconductor Switch P330 Ni Na, Guo Hui, Yuming Zhang , and Yimen Zhang
- 12.13 HightPowerParallelPlane4H-SiCPiNDiodeWithFP-Assisted-JTE TerminationP334Qingli Zheng, Yuming Zhang, and Yimen Zhang

ADC Circuits

13.1 An Optimized Design for a Decimation Filter and Implementation for Sigma- Delta ADC P338 Yingying Cui, Jie Huang, Lingjuan Wu, Xiaoxin Cui, Dunshan Yu 13.2 Design and Analysis of a Novel 8-bit 0.35-µm BiCMOS Pipelined ADC P342 Hongxia Liu, Gaijuan Xi, XiangHong Yu 13.3 A Digital Calibration Design for 10-bit Folding and Interpolating ADC Rong Fan, Kai Zhou, Zhuang Ma, Zhibiao Shao P346 13.4 A Dynamic Element Matching Technique for Multi-bit Quadrature **Delta-Sigma Modulators** P350 Chi-Tung Ko and Kong-Pang Pun 13.5 Design and Implementation of $\Sigma\Delta$ AD Converter P354 Jie Huang, Yingying Cui, Xiaoxin Cui, Dunshan Yu

Strained SiGe Materials and Devices

- 14.1 Analytical Modeling of Base Transit Time for a Si1-yGey **Heterojunction Bipolar Transistor** P358 Yeasir Arafat, Md. Ziaur Rahman Khan and M. M. Shahidul Hassan
- 14.2 Study on Hole Effective Mass of Strained Si1-xGex/(101)Si P362 JianJun Song, HeMing Zhang, HuiYo ng Hu, RongXi Xuan and XianYing Dai
- 14.3 Fabrication of High Compressive Stress Silicon Nitride Membrane in Strained Silicon Technology P365 Bin Shu, He-ming Z hang, Rong-xi X uan, Xian-ying Dai, Hui-y ong Hu, Jian-jun Song, Liang Liang, Jia-nan Cui
- 14.4 Collector Junction Depletion-Layer Transit Time Model of SiGe HBT with Space SiGe Layer P368

Huiyong Hu, Rui Chen, Heming Zhang, Jianjun Song

Power Devices & Management Circuits

- 15.1 Fast Speed Lateral IGBT with Buried N-region Controlled Anode on SOI Substrate P372 Wensuo Chen, Gang Xie, Bo Zha ng, Zhaoji Li and Mei Zhao
- 15.2 An Enhanced Double Current Limit Technique Used in High Power **BUCK Converter** P376

Zekun Zhou, Zhi Huang, Xing Ming, Bo Zhang, and Zhaoji Li

- 15.3 Integrated DC-DC Converter with an Auxiliary Output Stage for Transient Suppression P380 J. Wang, K. Ng, T. Kawashima, M. Sasaki, H. Nishio, and W.T. Ng
- 15.4 A CMOS Low-Dropout Regulator with High Power Supply Rejection P384 Wenguan Li, Ruohe Yao, and Lifang Guo
- 15.5 Design of novel full-load stabilized Low Dropout Regulator with high PSRR P388 David Suo, Jun Pan, Yonggui Hu, and Kaicheng Li
- 15.6 Single-inductor Dual-output DC/DC Buck converter With High full-load Efficiency P392 Junjie Qian, Zhibiao Shao

Wireless Circuit Structure

- **16.1 Multi-node Driving Circuits for Multi-branch Transmission Wires**Wu Fengfeng, Jia Song, Wang Yuan, Zhang GanggangP395
- 16.2 A New 12-bit Fully Differential SAR ADC for Wireless Implantable Neural Recording System P399

Y. C. Liang, B. Li, and Z. H. Wu

GaN Devices

- **17.1 GaN Smart Power Chip Technology** Kevin J. Chen, Hong Kong University of Science and Technology, HK, China
- 17.2 GaN Lattice Matched ZnO/Pr2O3 Film as Gate Dielectric Oxide Layer for AlGaN/GaN HEMT P408 Che-Kai Lin, Ming-Yang Chen, Hs iang-Chun Wang, Chih-Wei Yang, Chao-Wei Chiu, Hsien-Chin Chiu, Kuang-Po Hsueh
- 17.3 An Accurate Analytical Model for Current-Voltage Characteristics and TransConductance of AlmGa1-m/GaN MODFETs P412 Abtahi Hosseini, S. Ehsan1; Hosseini, S. Ebrahim
- 17.4 Effect of High Temperature AIN Interlayer on the Performance of AIGaN/GaN Properties P416 Junshuai Xue, Yue Hao, Jincheng Zhang, Jinyu NI
- 17.5 Characteristics Analysis of Gate Dielectrics in AlGaN/GaN MIS-HEMT P419 Zhiwei Bi , Yue Hao, Hongxia Liu, Linjie Liu, Qian Feng

Amplifier Circuits

- 18.1 Design Strategy for Two-Phase Switched Capacitor Step-Up Charge Pump P423 C. W. Kok, Canaan Microelectroncis Co. Hong Kong, China
- 18.2 A High Power Efficiency Class AB Switched-Opamp for Low Voltage

 Low Power Sigma-Delta Modulators
 P429

 Hanqing Wang, Jian Xu and Xiaobo Wu
- 18.3 Co-extraction Method for DC Model Parameters of BJT Based on
Global Optimization and Physical AnalysisP433
P433
Jiwei Sun, Xinzhang Jia, Hailong You, Zhiyun Li,

- 18.4 A Low Power Temperature Insensitive Voltage Supervisory Circuit in

 Metal Gate Technology
 P437

 Wing-Shan Tam, Oi-Ying Wong, Chi-Wah Kok, and Hei Wong
- 18.5 A Sub-1V CMOS Bandgap Reference with High-order Curvature Compensation P441 Zhidong Liu and Yuhua Cheng
- 18.6 An80-dBlinearbasebandCMOSVGAwithtemperaturecompensation for low-power applicationP445Qianqian Lei, Zhiming Chen, Yin Shi, Qiming Xu

Memory circuits

- 19.1 Material engineering in phase-change memory for low power
consumption and multi-level storageP449You Yin, Tomoyuki Noguchi, Hiroki Ohno, and Sumio Hosaka
- 19.2 Research of SBB Effect on SOI- MOSFET Low Power 4T SRAM CellZhuang Ma, Sichen Yu, Zhibiao ShaoP453
- 19.3 Diode Based Gate Oxide Anti-fuse One Time Programmable Memory
Array in Standard CMOS ProcessP457K. P. Ng, M. C. Lee, K. C. Kwong and Mansun ChanP457
- 19.4 SET and RESET State Resistance Modeling of Phase Change Memory P461

K. C. Kwong, Frank He and Mansun Chan

Nano Devices

- 20.1 Progressive-DegradationandBreakdownofW-La2O3MOSStructures after Constant Voltage StressP465J. Molina, E. Gutierre z, A. Jaco me, W. Calleja, F.J. De La Hidalga, P.Rosales, C. Zuñiga, C. Reyes, R. Torres and H. Iwai
- 20.2 Superior Contact Properties of Trench Filled Contact for 3D MOSFET Jae-Hyun Jung, Heon-Bok Lee, Jong-Bong Ha, Hee-Sung Kang, Jung-Hee Lee, and Sung-Ho Hahm P469
- 20.3 A Numerical Model for Solving Two Dimensional Poisson-Schrödinger Equation in Depletion All Around Operation of the SOI Four Gate Transistor P473 Shafat Jahangir, Ifat Jahangir and Q. D. M. Khosru

- 20.4 Effect of Material Composition, Device Length and Applied Voltage on Resonant Tunneling in an Asymmetrical Double-barrier Hetero-structure P477 Ifat Jahangir, Shafat Jahangir and Q. D. M. Khosru
- 20.5 Implementation of a Numerical Method for Quantum Drift-Diffusion Equations P481

M. B. Farahbakhsh1, S. E. Hosseini, H. Taghizadeh

SiC Microwave & Power Devices

- 21.1 Microwave power of S-Band 20mm SiC MESFETs
 P484

 CHEN Gang, CHEN Zheng, BAI Song, WU Peng, LI ZheYang, FENG

 Zhong
- 21.2 Simulation study on Field-Plated Buried Gate-Buried Channel SiC MESFETs P487

Rui Zhang, Hongliang Lu, Yimen Zhang and Yuming Zhang

21.3 The effect of the surface recombination on current gain for 4H-SiC BJT P491 Yourup Zhang, Do Zhang, Zhaoji Li, Viacobuon Dong, and Vilin liu

Yourun Zhang, Bo Zhang, Zhaoji Li, Xiaochuan Deng, and Xilin liu

- 21.4 The influence of interface states on the current gain of 4H-SiC bipolar transistors P495 Hongliang Lu, Yimen Zhang, Yuming Zhang, Ming Sun
- 21.5 Design and Optimization of Junction Termination Technology for 4H-SiC BJTs P498

Qian Zhang, Yuming Zhang, Yimen Zhang

Optical Devices

- **22.1 Characterization of Quantum-Well and Super-Lattice Lasers P501** H. C. Tseng, A. H. Wu,C. Hu, C. T. Wan, Y. K. Su and S. Tsau
- 22.2 The Photo-generated Parasitical Capacitance Model of GaN-based Pin Ultraviolet Detector P505 Bo Gao, Hongxia Liu, Qianwei Kuang, Wen Zhou, Lei Cao
- 22.3 Electronic structures and optical properties of nitrogen-doped SiC nanotube P509

Jiuxu Song, Yintang Yang, Hongxia Liu

22.4 Enhanced Performance for OTFT on Glass with HfO2 as Gate Dielectric by UV-Ozone Treatment P513 W.M. Tang, M.G. Helander, M.T. Greiner, G. Dong, W.T. Ng and Z.H. Lu

Memory Device and Technology

- 23.1 A High Speed Low Power Capacitorless SOI-DRAM Cell Using Impact Ionization and GIDL Effect P517 Jianing Hou, Zhibiao Shao, Xin Miao
- 23.2 Fabrication and Electrical Characterization of MONOS Memory with Novel High- κ Gate Stack P521 L. Liu, J. P. Xu, C. L. Chan, P. T. Lai
- 23.3 Design Optimization in Write Speed of Multi-Level Cell Application for Phase Change Memory P525 Jun-Tin Lin, Yi-Bo Liao, Meng-H sueh Chiang, I-Hsua n Chiu, Chia-Long Lin, Wei-Chou Hsu, Pei- Chia Chiang, Shy h-Shyuan Sheu, Yen- Ya Hsu, Wen-Hsing Liu, Keng-Li Su, Ming-Jer Kao, and Ming-Jinn Tsai
- 23.4 Numerical Simulation of Programming and Read Process for Nano-Scale Phase-Change Memory (PCM) Cell P529 Yiqun Wei, Laidong Wang, Wei Wang, Xinnan Lin, Frank He, Mansun Chan and Xing Zhang

Author Index